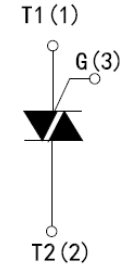
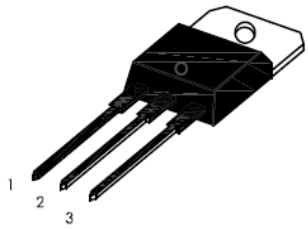
High current density due to double mesa technology; SIPOS and Glass Passivation. IPT04Q08-xx series are suitable for general purpose AC Switching. They can be used as an ON/OFF function In application such as static relays, heating regulation, Induction motor stating circuits… or for phase Control operation light dimmers, motor speed Controllers.





TO-220B

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM} / V_{RRM}	800	V
I_{GT}	5 to 25	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage Junction Temperature Range Operating Junction Temperature Range	Tstg Tj	-40 to +150 -40 to +125	℃
Repetitive Peak Off-state Voltage Tj = 25℃ Repetitive Peak Reverse Voltage	V_{DRM} V_{RRM}	800 800	V
Non Repetitive Peak Off-state Voltage Tj = 25℃ Non Repetitive Peak Reverse Voltage	V_{DSM} V_{RSM}	900 900	V
RMS on–state current Tc =105℃ (Full sine wave)	$I_{T(RMS)}$	4	A
Non repetitive surge peak on–state Current f = 60Hz t = 16.7ms (full cycle, Tj = 25℃) f = 50 Hz t = 20ms	I_{TSM}	38 35	A
I^2t Value for fusing tp = 10ms	I^2t	6	A^2s
Critical Rate of rise of on-state current I_G = 2xI_{GT}, tr ≤ 100ns, f = 120Hz, Tj = 125 ℃	dI / dt	50	A/us
Peak gate current tp = 20us, Tj = 125 ℃	I_{GM}	4	A
Average gate power dissipation Tj = 125 ℃	$P_{G(AV)}$	1	W

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ELECTRICAL CHARACTERISTICS (Tj = 25 ℃ unless otherwise specified)

Symbol	Test Condition	Quadrant		IPT04Q08-xxB				Unit
				TE	DE	SE	AE	
I_{GT}	V_D = 12V R_L = 30Ω	I – II – III IV	MAX	5 5	5 10	10 10	10 25	mA
V_{GT}		ALL	MAX	1.5				V
V_{GD}	V_D=V_{DRM}, R_L=3.3KΩ, Tj = 125 ℃	ALL	MIN	0.2				V
I_L	I_G = 1.2 I_{GT}	I – III – IV	MAX	10	10	20	20	mA
		II		20	20	40	40	
I_H	I_T = 500mA		MAX	15	15	25	25	mA
dV/dt	V_D = 67% V_{DRM} gate open Tj = 125 ℃		MIN	10	10	10	10	V/us
(dV/dt)c	(dV/dt) c=0.8A/ms Tj = 125 ℃		MIN	1	1	5	5	V/us

STATIC CHARACTERISTICS

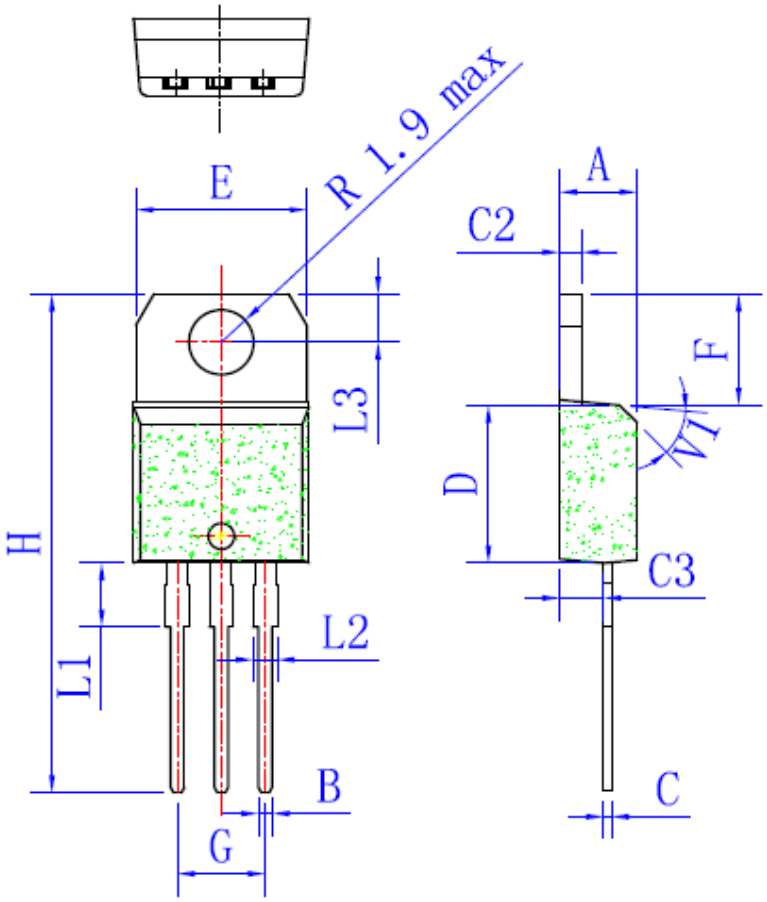
Symbol	Test Conditions		Value (MAX)	Unit
V_{TM}	I_{TM} = 5.5A, t p = 380uS	Tj = 25 ℃	1.6	V
I_{DRM}	V_D = V_{DRM}	Tj = 25 ℃	5	uA
I_{RRM}	V_R = V_{RRM}	Tj = 125 ℃	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R_{th} (j – c)	Junction to case (AC)	2.6	℃/W

PACKAGE MECHANICAL DATA

TO-220B



	Millimeters		
	Min	Typ	Max
A	4.4		4.6
B	0.61		0.88
C	0.46		0.70
C2	1.23		1.32
C3	2.4		2.72
D	8.6		9.7
E	9.8		10.4
F	6.2		6.6
G	4.8		5.4
H	28		29.8
L1		3.75	
L2	1.14		1.7
L3	2.65		2.95
V		40°	

FIG.1: Maximum power dissipation versus RMS on-state current(full cycle)

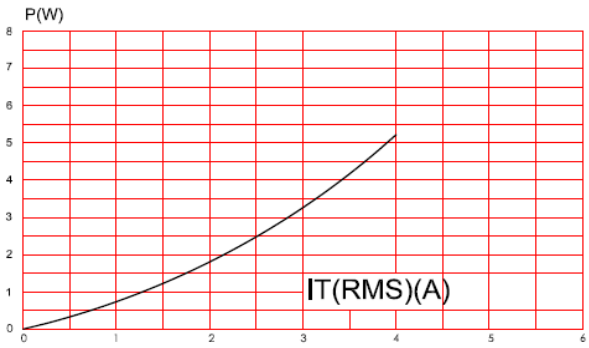


FIG.2: RMS on-state current versus case temperature(full cycle)

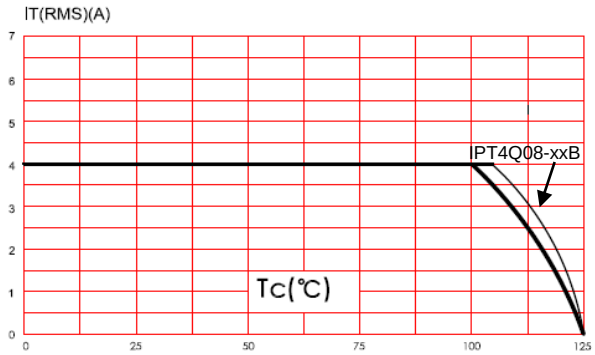


FIG.3: On-state characteristics (maximum values)

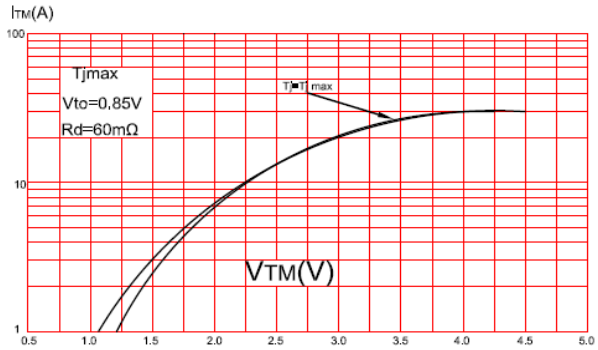


FIG.4: Surge peak on-state current versus number of cycles

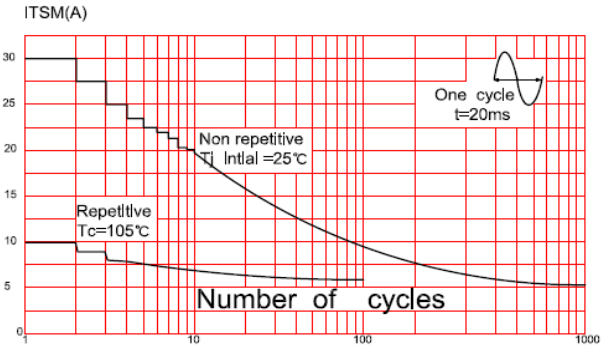


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10ms.

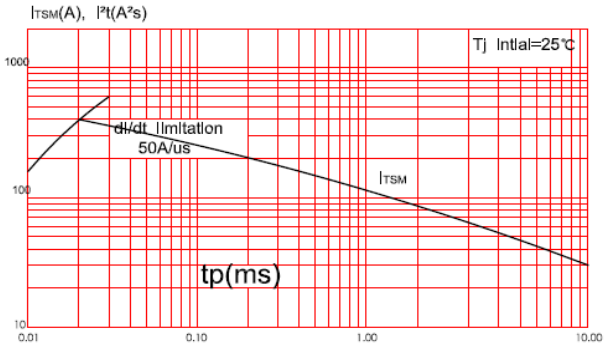


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature(typical values)